

TRANSIL™ array for data protection

Main applications

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

- Computers
- Printers
- Communication systems
- Cellular phones handsets and accessories
- Wireline and wireless telephone sets
- Set top boxes

Features

- 2 up to 5 Unidirectional Transil functions
- Breakdown voltage:
 $V_{BR} = 6.1 \text{ V min. and } 25 \text{ V min.}$
- Low leakage current: $< 1 \mu\text{A}$
- Very small PCB area $< 4.2 \text{ mm}^2$ typically

Description

The ESDAxxxWx are monolithic suppressors designed to protect components connected to data and transmission lines against ESD.

These devices clamp the voltage just above the logic level supply for positive transients, and to a diode drop below ground for negative transients.

Benefits

- High ESD protection level: up to 25 kV
- High integration

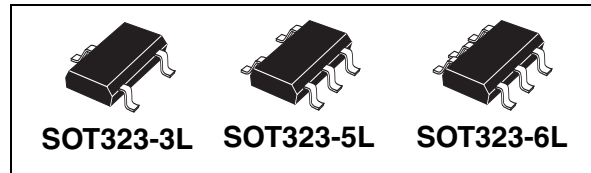
Complies with the following standards

IEC61000-4-2

Level 4 15 kV (air discharge)
 8 kV (contact discharge)

MIL STD 883E - Method 3015-7 Class 3

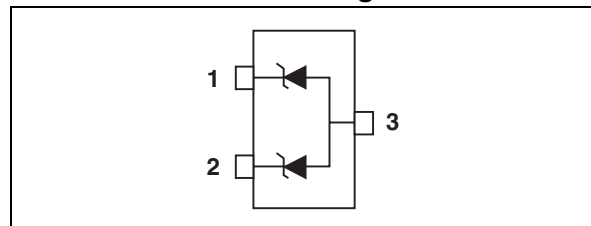
25 kV HBM (Human Body Model)



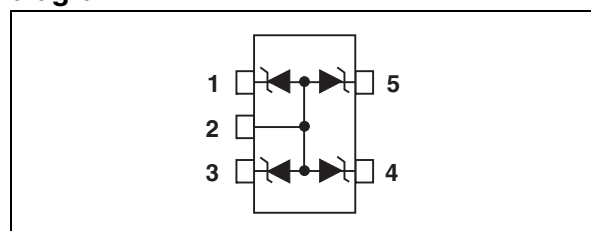
Order codes

Part Numbers	Marking
ESDA6V1W5	E61
ESDA6V1-5W6	E62
ESDA25W	E25
ESDA25W5	E25

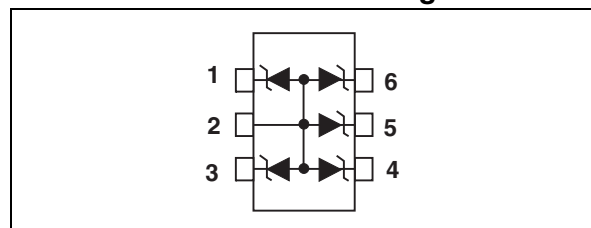
ESDA25W Functional diagram



ESDA6V1W5/ESDA25W5 Functional diagram



ESDA6V1-5W6 Functional diagram



1 Characteristics

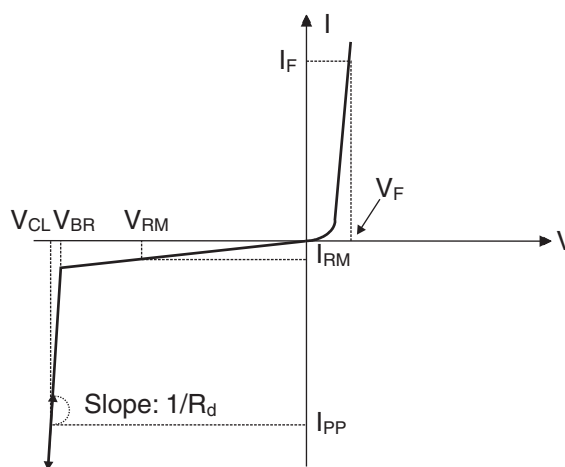
Table 1. Absolute Ratings ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit	
P_{PP}	Peak pulse power (8/20 μs)	ESDA25W	400	W
		ESDA25W5 / ESDA6V1W5	150	
		ESDA6V1-5W6	100	
T_j	Junction temperature	125	$^{\circ}\text{C}$	
T_{stg}	Storage temperature range	-55 to +150	$^{\circ}\text{C}$	
T_L	Maximum lead temperature for soldering during 10s	260	$^{\circ}\text{C}$	
T_{op}	Operating temperature range ⁽¹⁾	ESDA25W / ESDA25W5 / ESDA6V1W5	-40 to +125	$^{\circ}\text{C}$
		ESDA6V1-5W6	-40 to +125	

1. The values of the operating parameters versus temperature are given through curves and αT parameter.

1.1 Electrical Characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter
V_{RM}	Stand-off voltage
V_{BR}	Breakdown voltage
V_{CL}	Clamping voltage
I_{RM}	Leakage current
I_{PP}	Peak pulse current
I_R	Reverse leakage current
I_F	Forward current
αT	Voltage temperature coefficient
V_F	Forward voltage drop
C	Capacitance
R_d	Dynamic resistance



Part Numbers	V_{BR}			I_{RM} @ V_{RM}		V_F @ I_F		R_d	αT	C
	min.	max.	@ I_R			max.		typ. ⁽¹⁾	max. ⁽²⁾	typ.
	V	V	mA	μA	V	V	mA	Ω	$10^{-4}/^{\circ}C$	pF
ESDA25W	25	30	1	1	24	1.2	10	1.1	10	65
ESDA25W5	25	30	1	1	24	1.2	10	1.9	10	30
ESDA6V1-5W6	6.1	7.2	1	1	3	1.25	200	0.61	6	50
ESDA6V1W5	6.1	7.2	1	1	3	1.25	200	0.35	6	90

1. Square pulse $I_{pp} = 15 A$, $t_p = 2.5 \mu s$
2. $V_{BR} = aT * (T_{amb} - 25^{\circ}C) * V_{BR}(25^{\circ}C)$

Figure 1. Peak power dissipation versus initial junction temperature

Figure 2. Peak pulse power versus exponential pulse duration (T_j initial = 25°C) (ESDA25W)

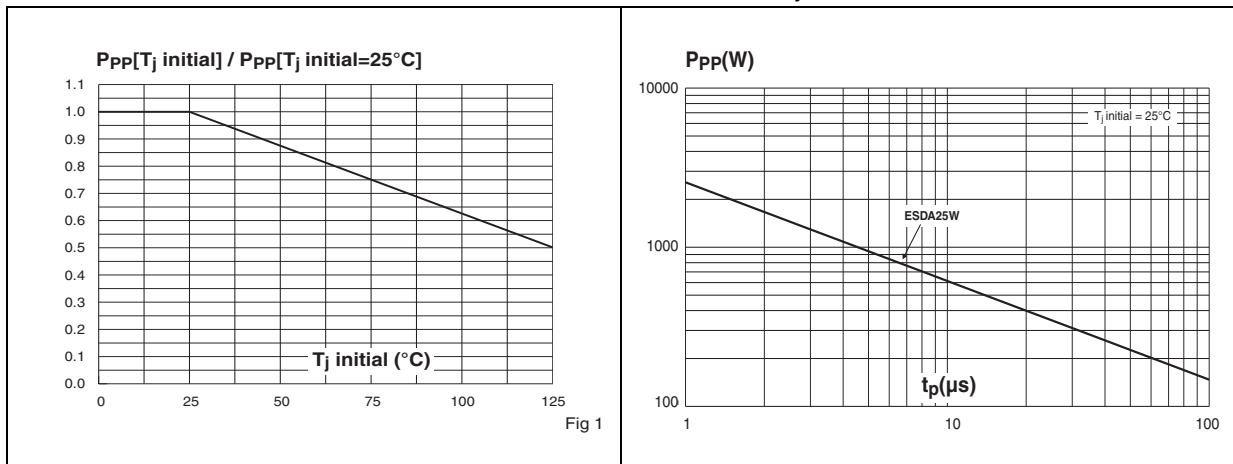


Figure 3. Peak pulse power versus exponential pulse duration (T_j initial = 25°C) (ESDA25W5 / ESDA6V1W5 / ESDA6V1-5W6)

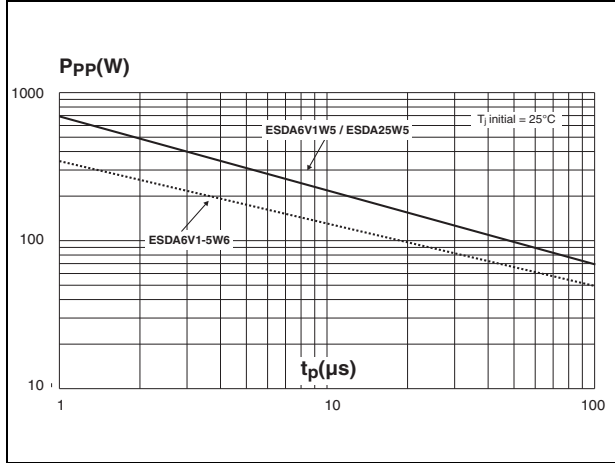


Figure 4. Clamping voltage versus peak pulse current (T_j initial = 25°C, rectangular waveform, $t_p = 2.5 \mu$ s) (ESDA25W / ESDA25W5)

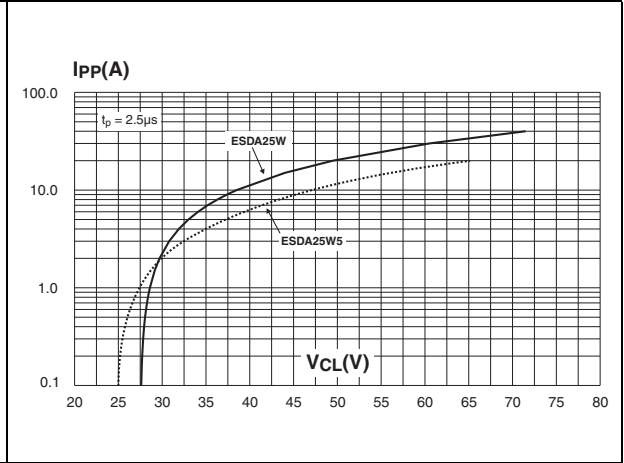


Figure 5. Clamping voltage versus peak pulse current (T_j initial = 25°C, rectangular waveform, $t_p = 2.5 \mu$ s) (ESDA6V1W5 / ESDA6V1-5W6)

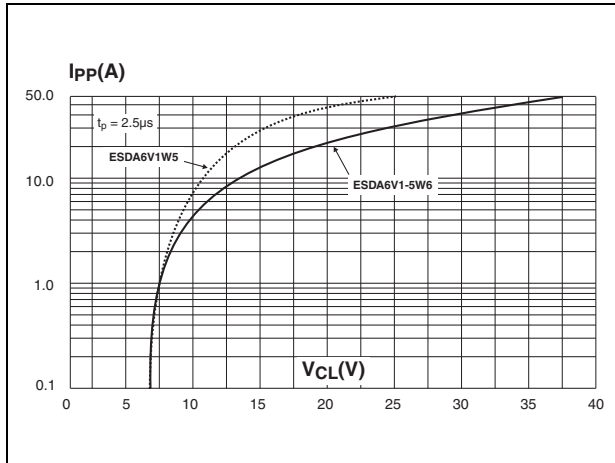


Figure 6. Capacitance versus reverse applied voltage (typical values) (ESDA25W / ESDA25W5)

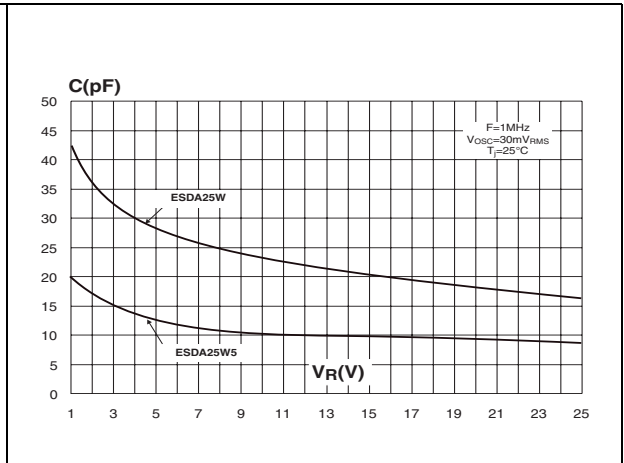


Figure 7. Capacitance versus reverse applied voltage (typical values) (ESDA6V1W5 / ESDA6V1-5W6)

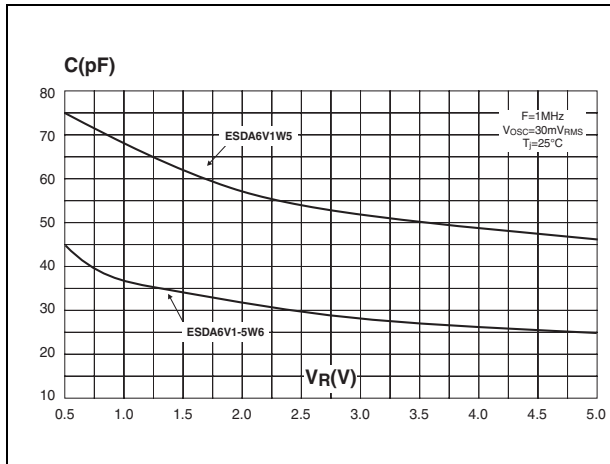


Figure 8. Relative variation of leakage current versus junction temperature (typical values)

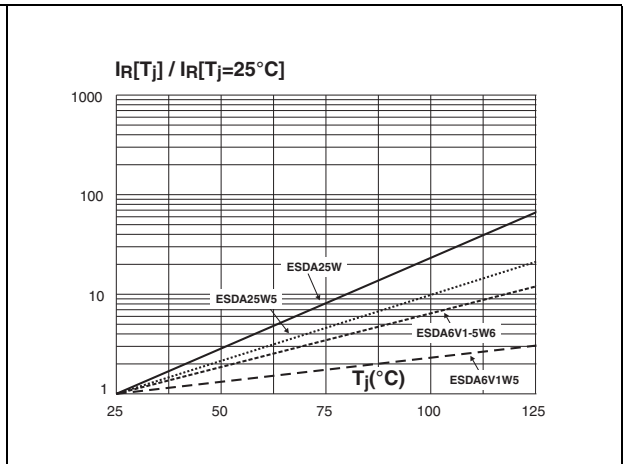


Figure 9. Peak forward voltage drop versus peak forward current (typical values) (ESDA25W / ESDA25W5)

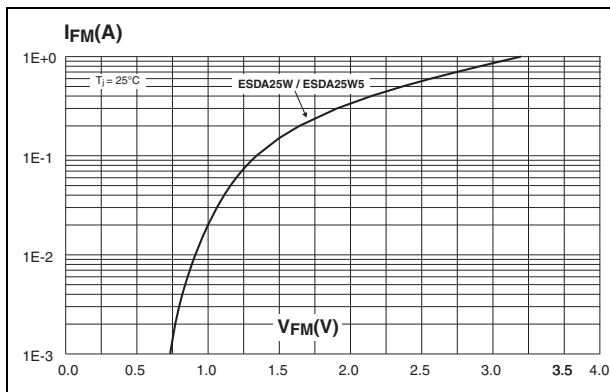


Figure 10. Peak forward voltage drop versus peak forward current (typical values) (ESDA6V1W5 / ESDA6V1-5W6)

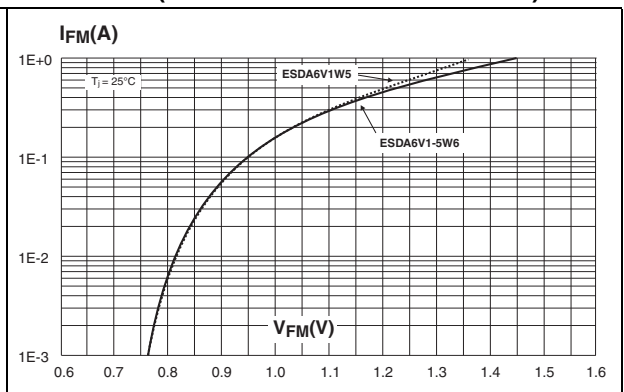
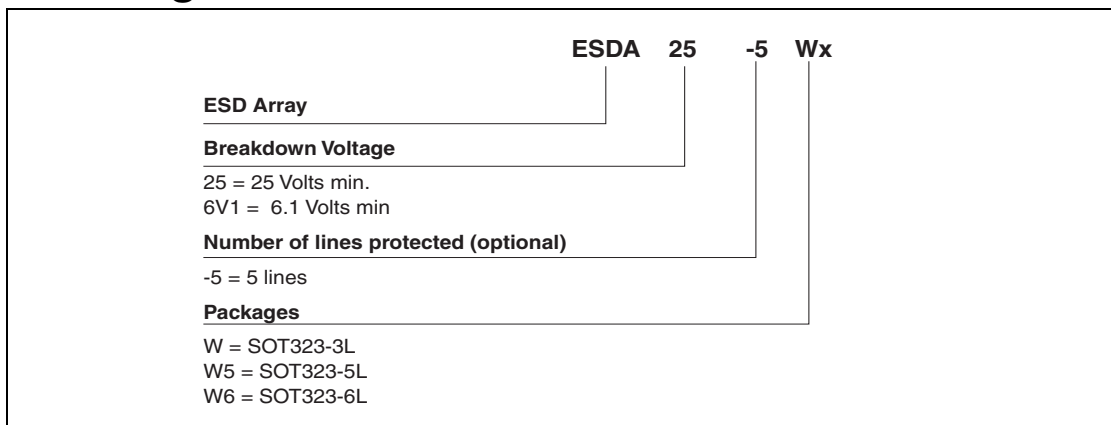


Figure 11. ESD response to IEC61000-4-2 (air discharge 15 kV, positive surge)



2 Ordering information scheme



3 Package mechanical data

3.1 SOT323-3L package

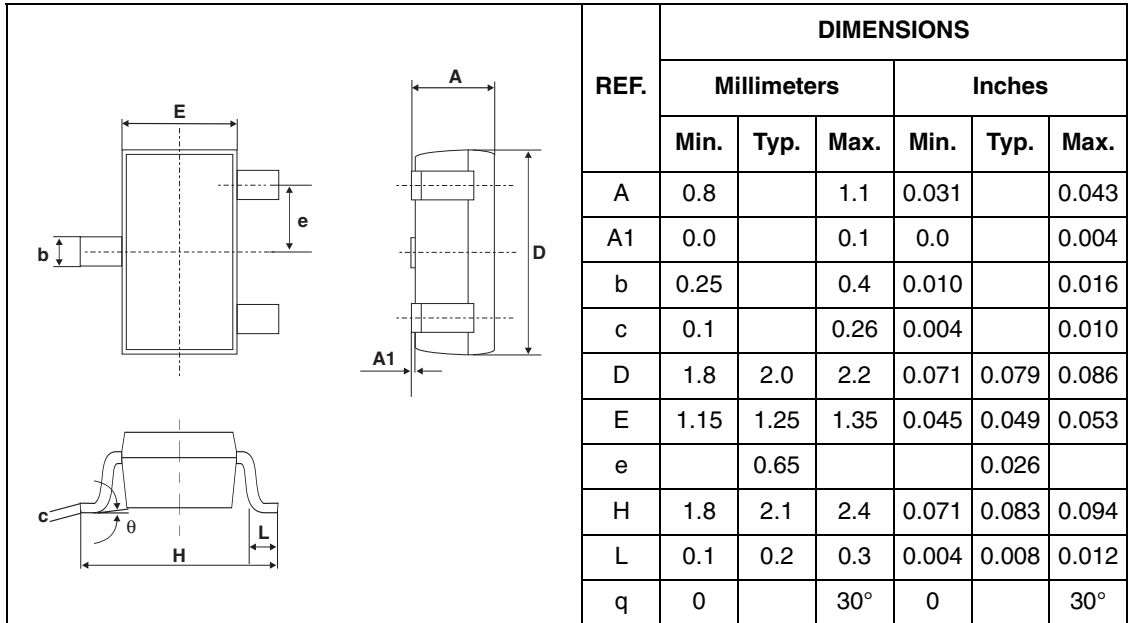
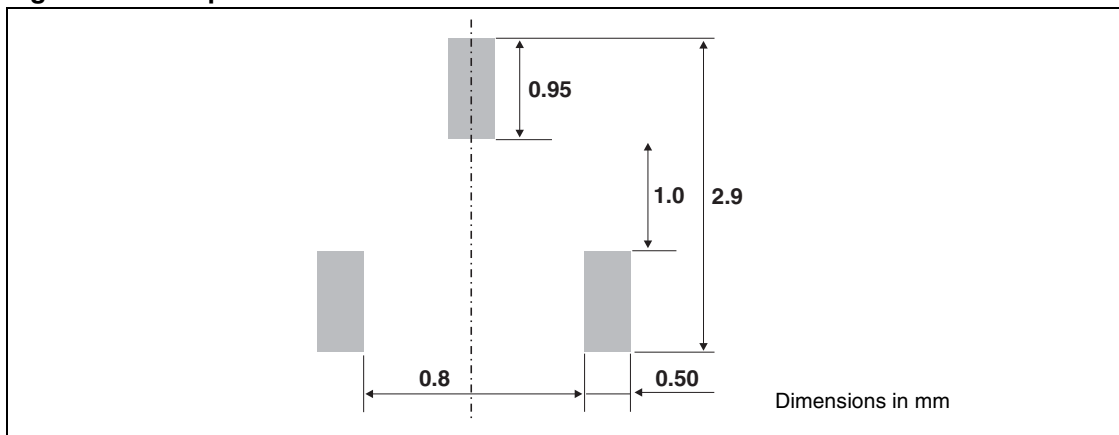


Figure 12. Footprint dimensions



3.2 SOT323-5L package

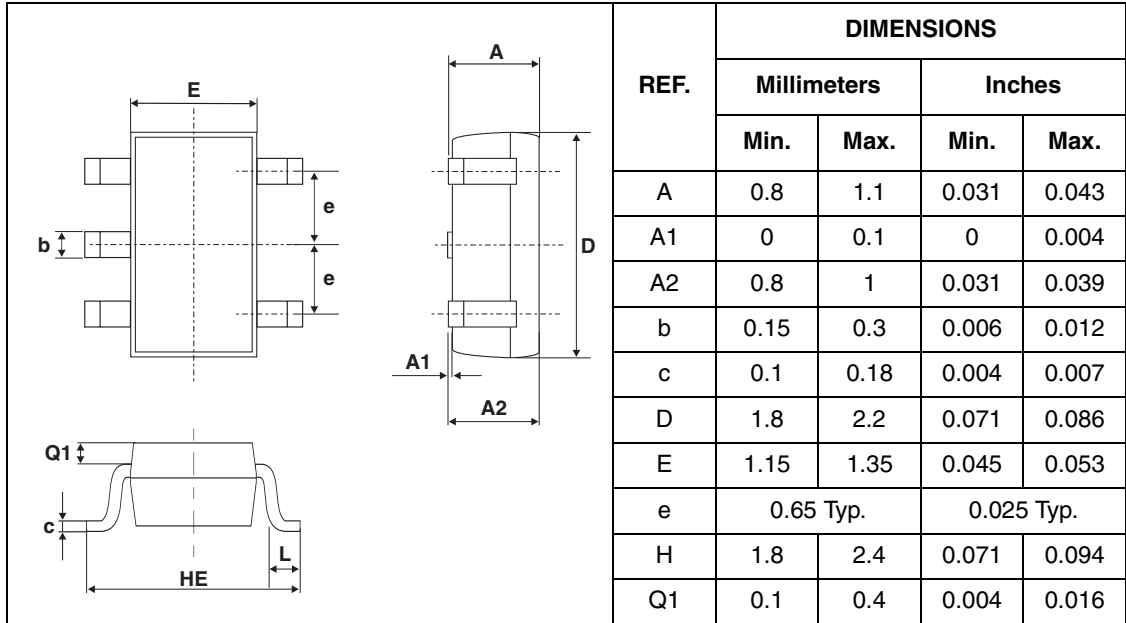
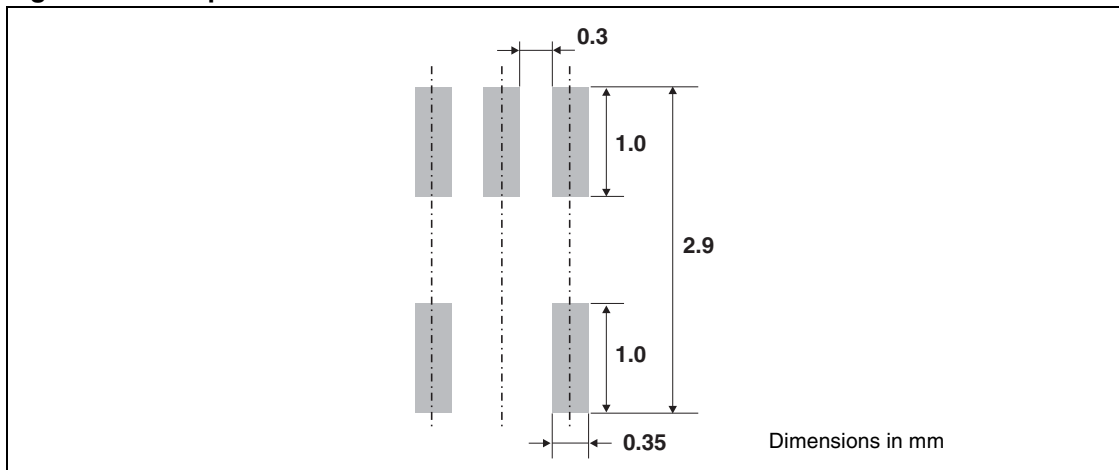


Figure 13. Footprint dimensions



3.3 SOT323-6L package

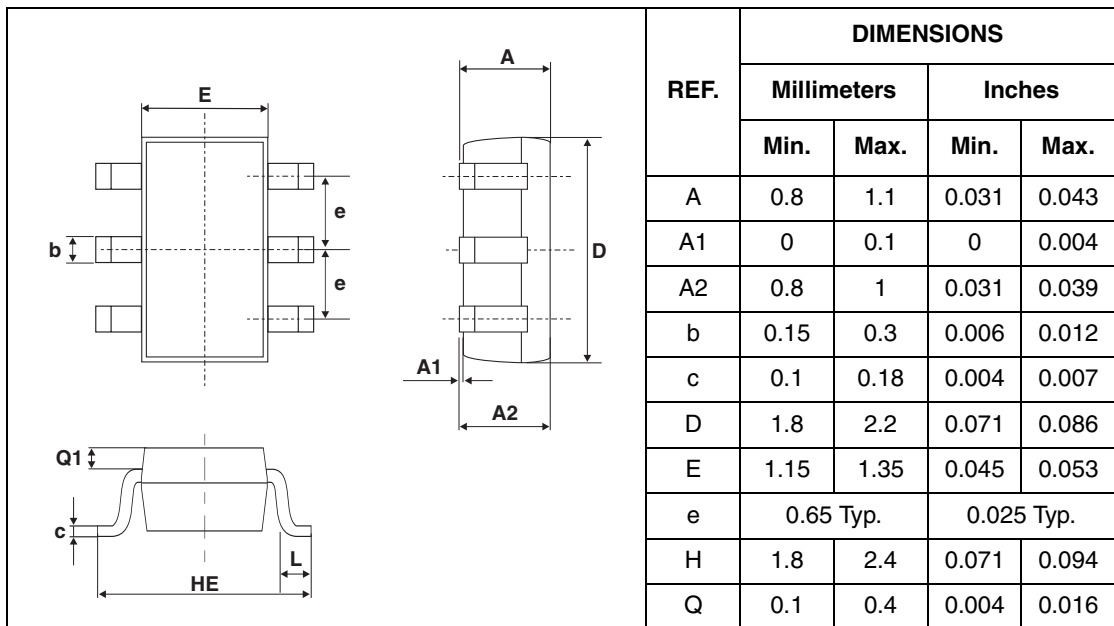
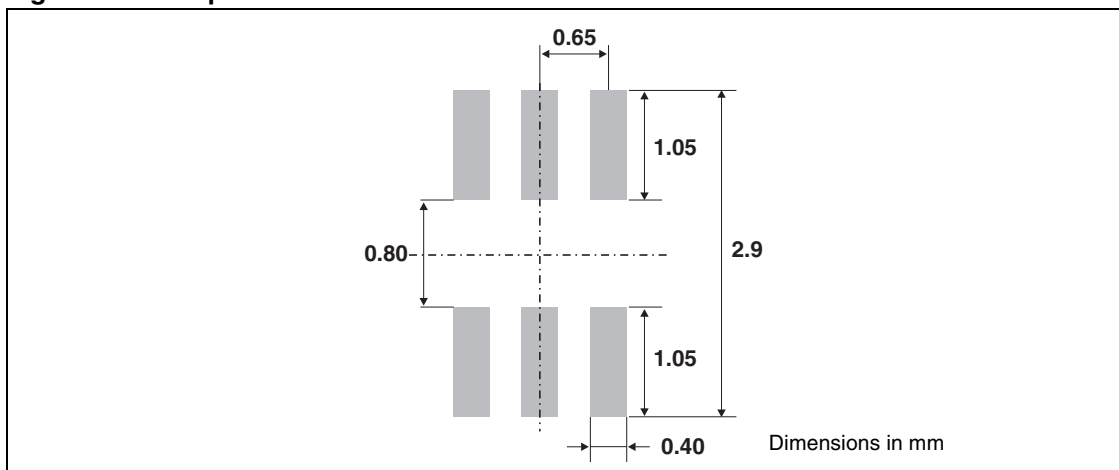


Figure 14. Footprint dimensions



4 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
ESDA6V1W5	E61	SOT323-5L	6 mg	3000	Tape & reel
ESDA6V1-5W6	E62	SOT323-6L			
ESDA25W	E25	SOT323-3L			
ESDA25W5	E25	SOT323-5L			

5 Revision history

Date	Revision	Changes
20-Jul-2005	1	Initial release
29-Aug-2005	2	Added notes to table on page2, removed annotations in Figure 1.

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



单击下面可查看定价，库存，交付和生命周期等信息

[>>STMicro\(意法半导体\)](#)